

# Development of Nb<sub>3</sub>Sn (and Bi-2212) strands in preparation for the FCC

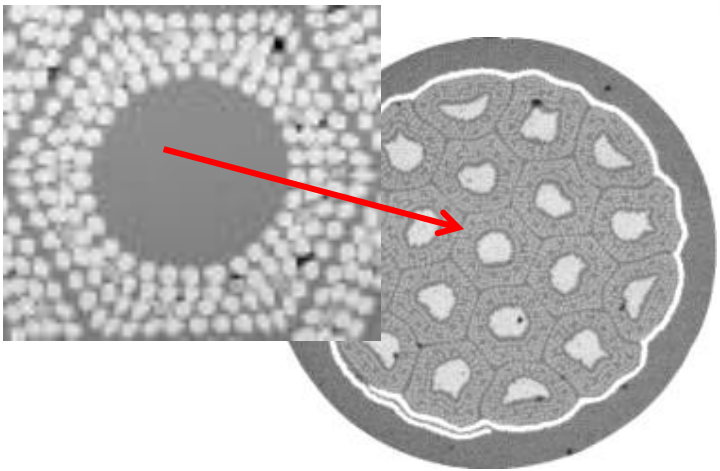
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Oxford Superconducting Technology, Carteret, NJ 07008 USA

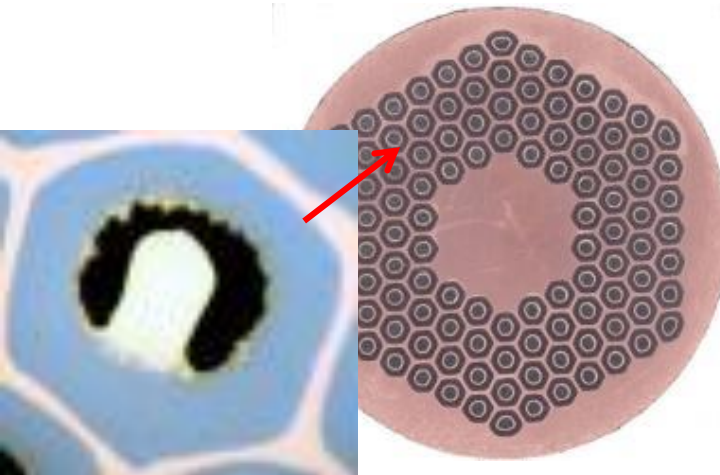
- The work summarized in this talk reflects more than 15 years of continuous financial and intellectual support
  - U.S. DOE - High Energy Physics
  - European Organization for Nuclear Research (CERN)
  - Lawrence Berkeley National Laboratory
  - Fermi National Accelerator Laboratory
  - Brookhaven National Laboratory
  - ASC - Florida State University / NHMFL
- Thank you for your continued support and collaborations

- Nb<sub>3</sub>Sn FCC conductor: a significant challenge!
  - Incremental improvement opportunities if  $D_{\text{eff}} \sim 60 \mu\text{m}$
  - Renewed need for more fundamental Nb<sub>3</sub>Sn R&D
- Properties of present Nb<sub>3</sub>Sn accelerator strand
- Bi-2212 development progress
- Nb<sub>3</sub>Sn is not Nb-Ti: Review of conductor cost drivers
- Bridging technical and industrial gaps until the FCC

# Nb<sub>3</sub>Sn is an engineering material



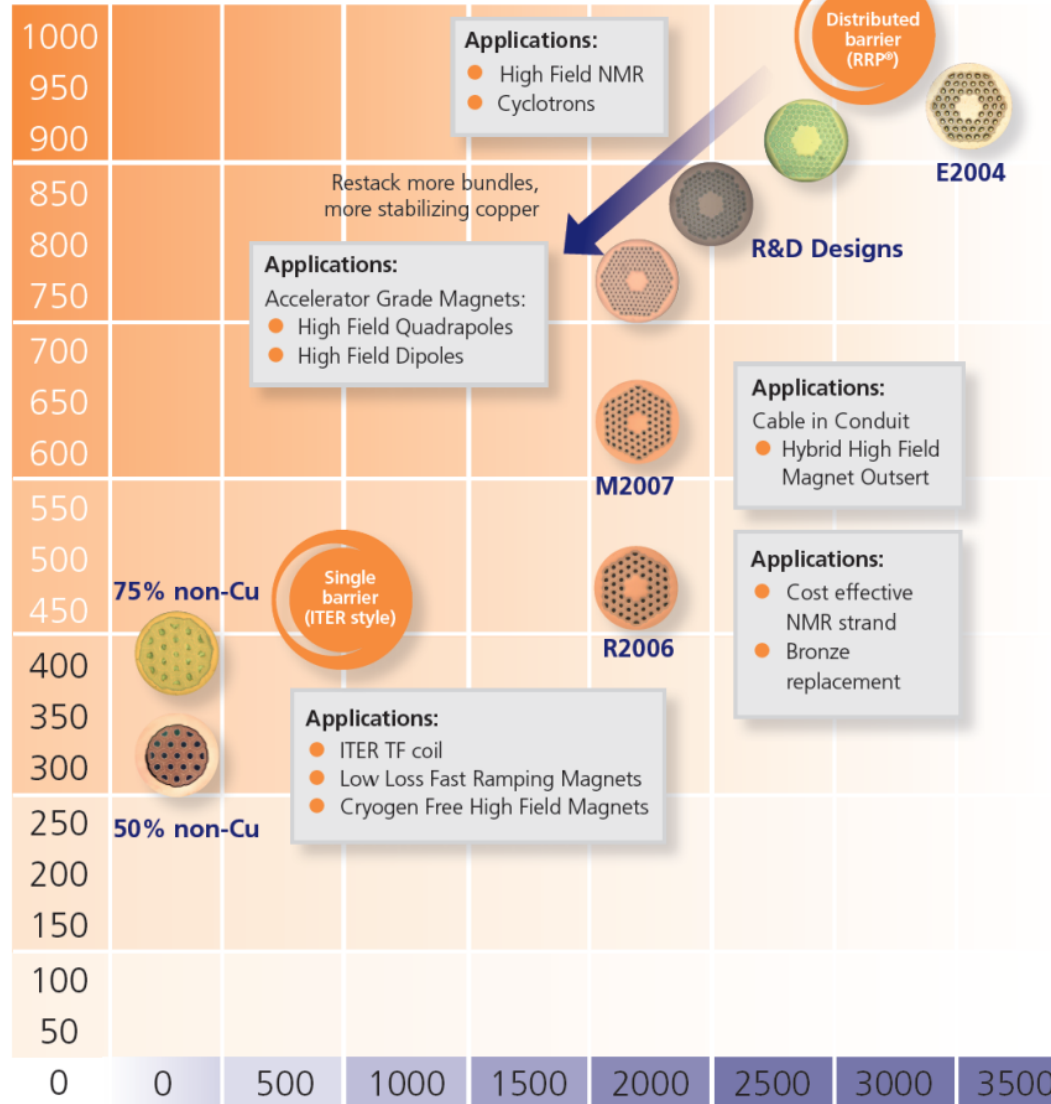
Single Barrier – Discrete filaments, low  $J_c$



Distributed Barrier RRP® – high Nb% and Sn%

$I_c$  (12 T, 4.2 K)  
in Amps

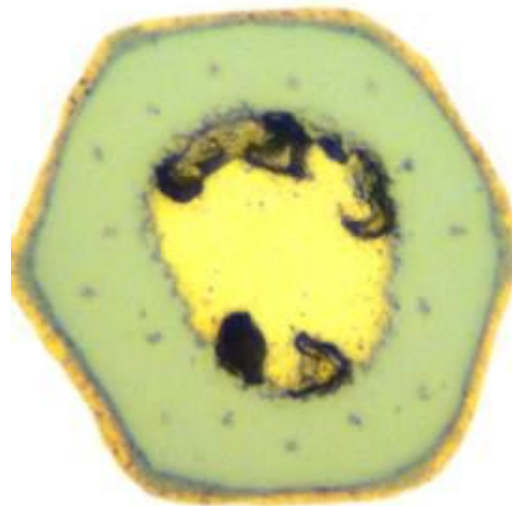
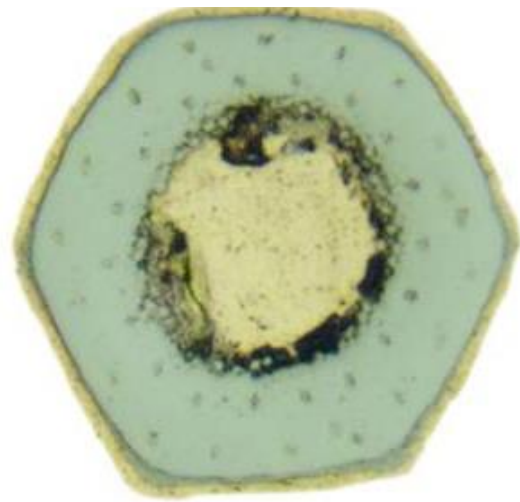
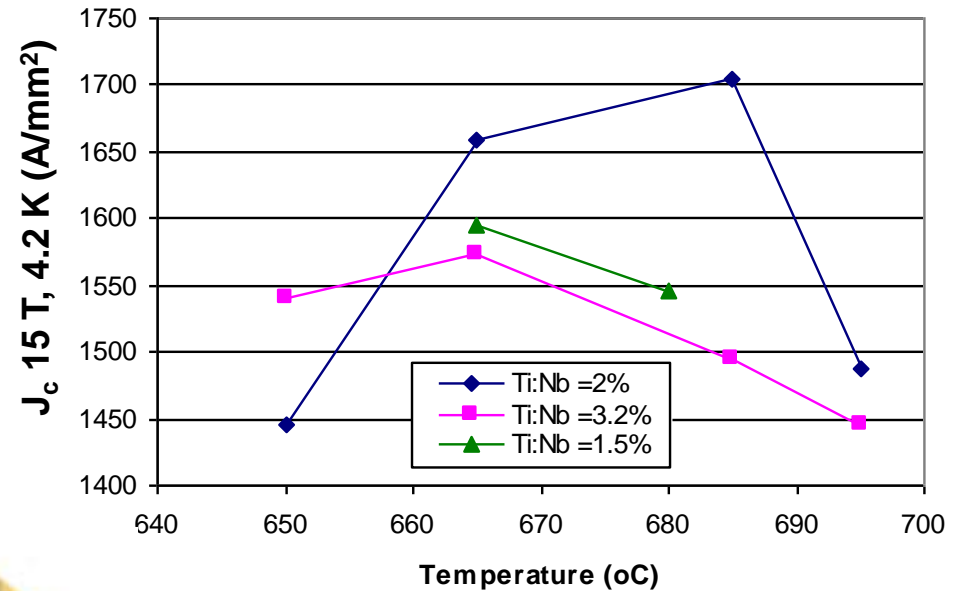
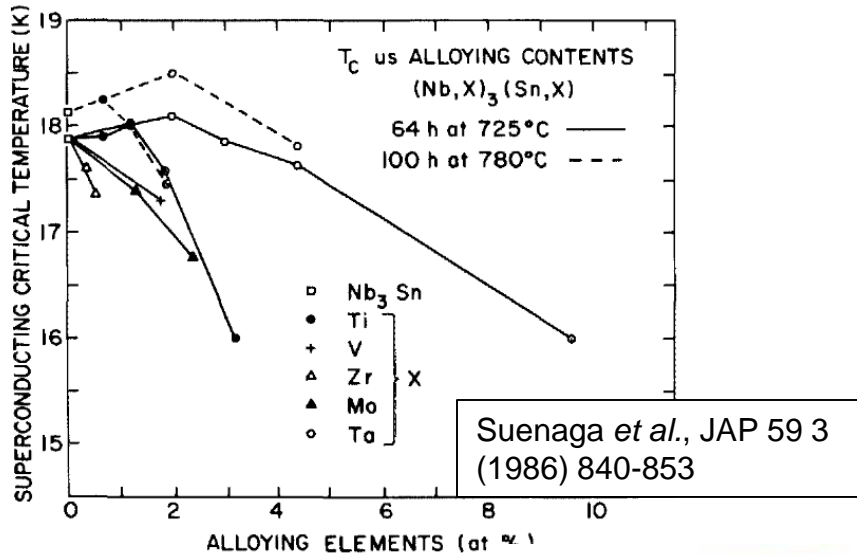
0.8mm  $I_c$  (12T, 4.2K) in A  
Increasing magnetic field strength



0.8mm Non-Copper Magnetization Hysteresis Loss ( $mJ/cm^3$ )

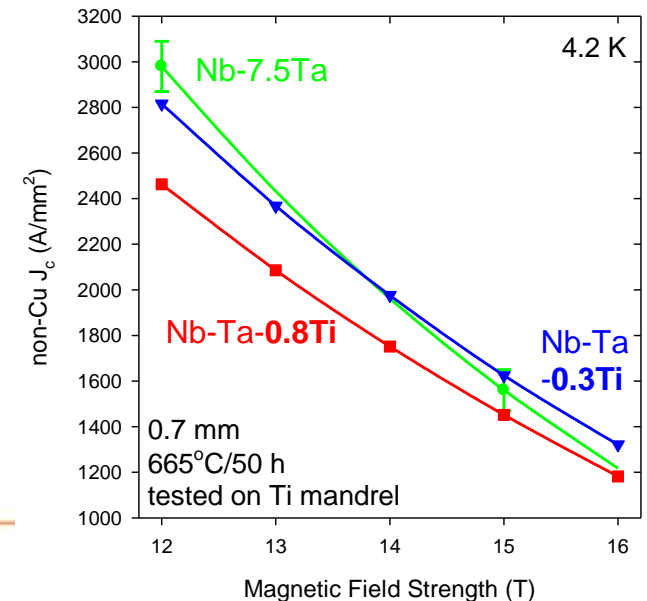
Faster Ramping Magnets Decreasing Flux Jumps

# From materials science to actual strands



Nb-7.5 Ta-0.8 Ti

Nb-7.5 Ta-0.3 Ti

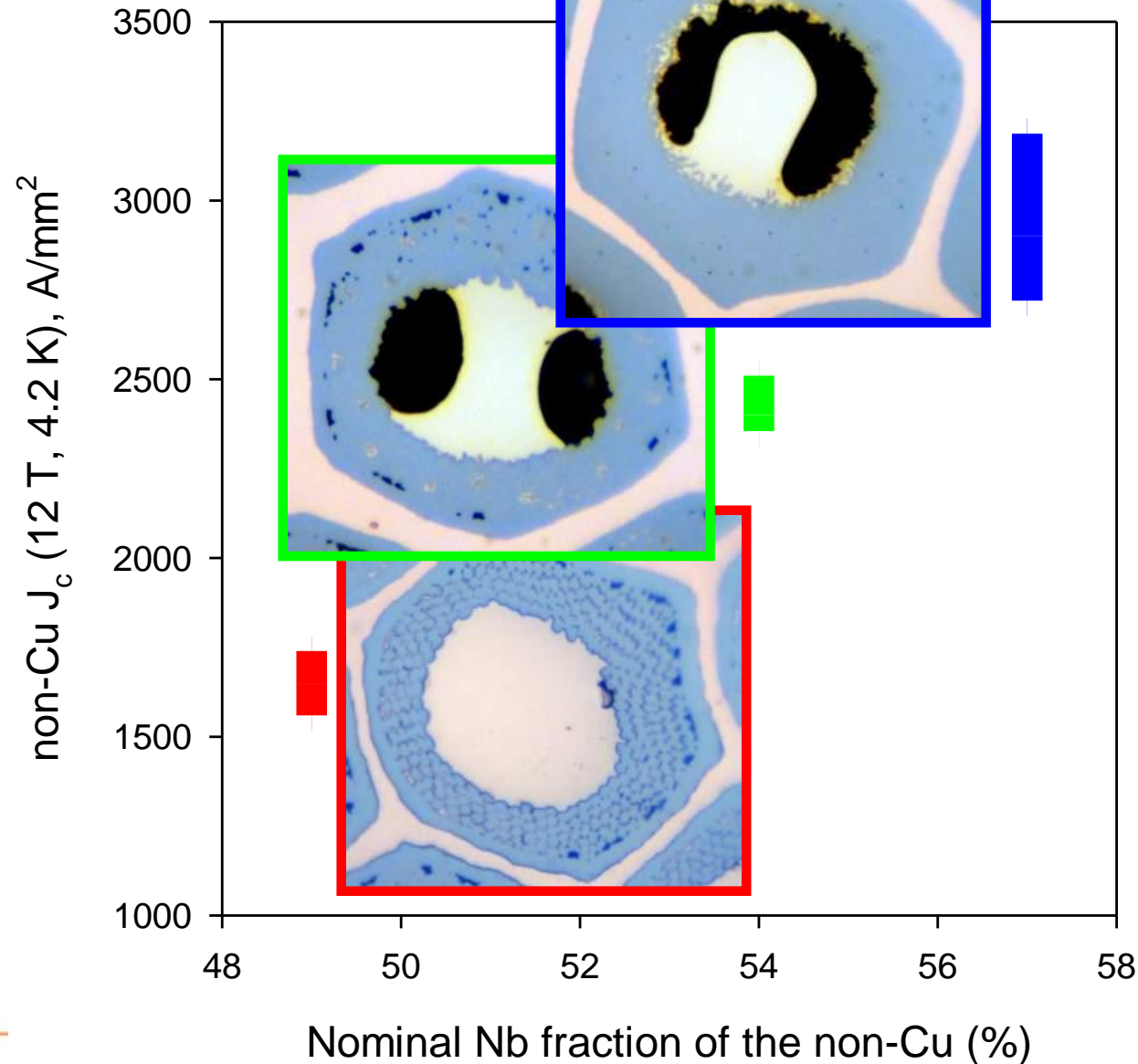


# Strand cross sectional area optimization

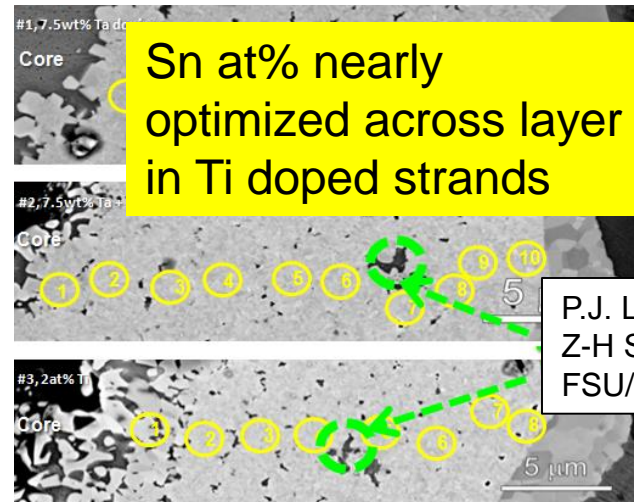
More Nb =  
Less Cu

More Nb  
(+Sn) =  
*More Nb<sub>3</sub>Sn*

Less Cu +  
More Sn =  
*Better Nb<sub>3</sub>Sn*

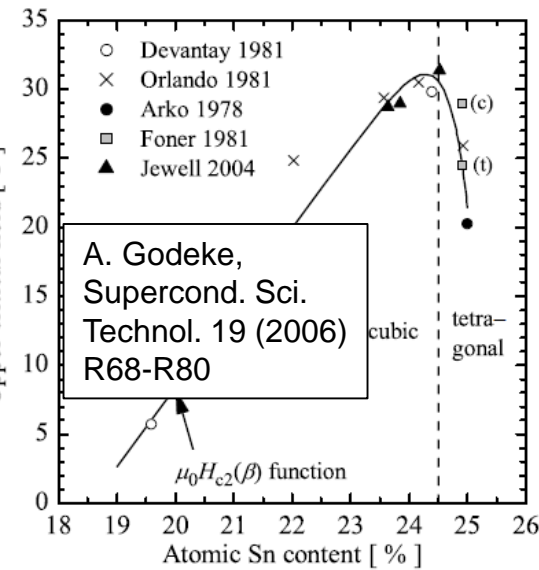
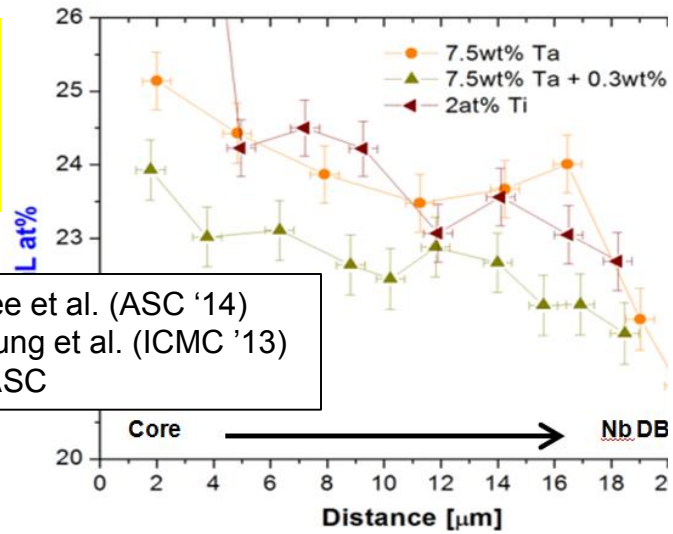


# Present strands: $J_c$ already nearly optimized(?)



Sn at% nearly optimized across layer in Ti doped strands

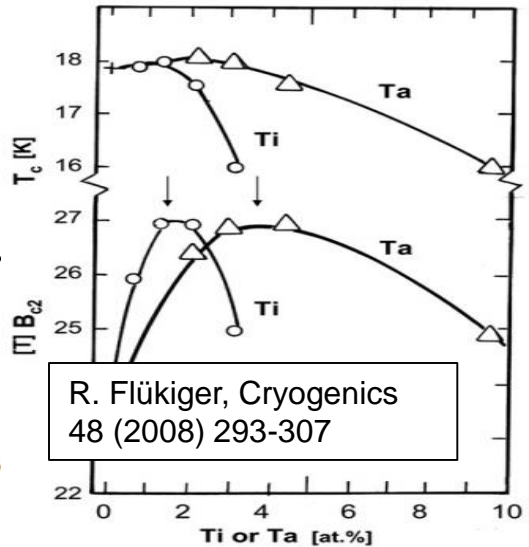
P.J. Lee et al. (ASC '14)  
Z-H Sung et al. (ICMC '13)  
FSU/ASC



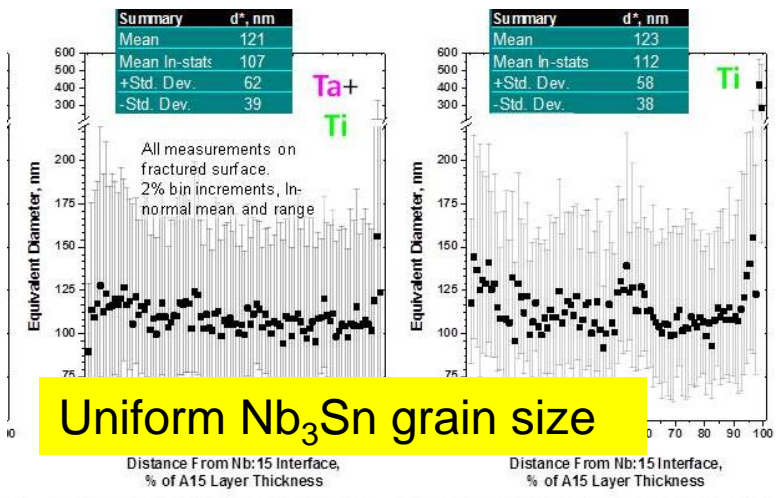
A. Godeke, Supercond. Sci. Technol. 19 (2006) R68-R80

Heat treatment Temp (°C)	Time (h)	$T_{c,onset}$ (K)	$T_{c,mid}$ (K)
620	192	18.10	16.83
650	96	18.09	17.06
665	50	18.31	17.14
680	48	18.40	17.24
695	48	18.36	17.51
750	96	18.34	17.57

C. Tarantini et al., SuST 27 (2014) 065013



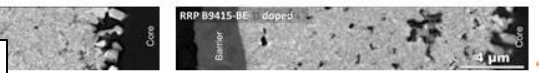
R. Flükiger, Cryogenics 48 (2008) 293-307



Uniform  $Nb_3Sn$  grain size

Ti doping close to optimal

P.J. Lee et al. (ASC 2014)



RRP B9415-BE Ti doped

# Target FCC Nb<sub>3</sub>Sn strand performance

Ballarino and Bottura, *IEEE Trans Appl. Supercond.* **25**, (2015).

Property	Units	Target	RRP®	Single barrier
Strand diameter	(mm)	0.5 - 1.0 mm		
J <sub>c</sub> (4.2 K, 16 T)	(A/mm <sup>2</sup> )	≥ 1500	? Need ↑ 25%	
Filament size (D <sub>eff</sub> )	(μm)	≤ 20	? Need ↓ 50%	
RRR		≥ 150		
Unit Length	(km)	≥ 5 km	? 1 billet = 9 km @ 0.85 mm	
Cost (@ 12 T, 4.2 K)	€/kA·m	1/3 of today's costs of approximately €10/kA·m		

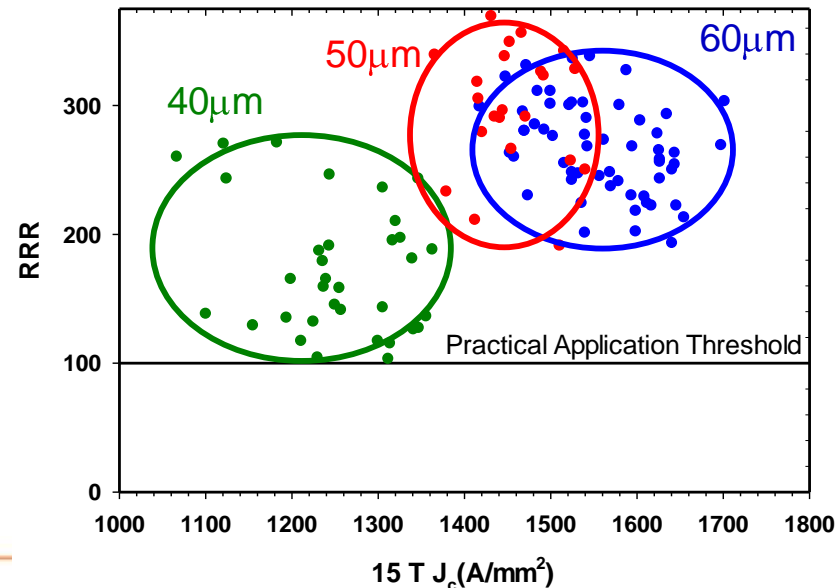
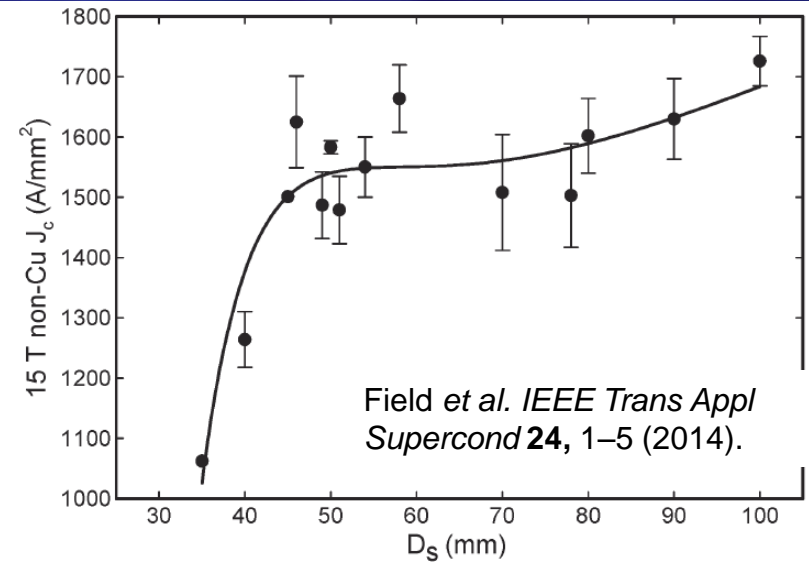
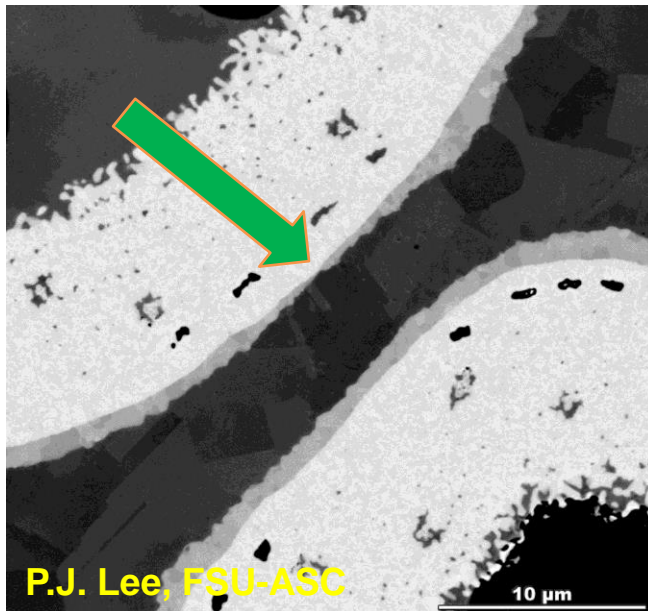
- Only distributed barrier strands come close to target J<sub>c</sub>
- Internal tin billets are not extruded → limited billet mass, maximum length

Focus on distributed barrier, RRP® strand



# Reducing the effective filament diameter seems to be the largest challenge

- Means to keep RRR high:
    - Use less Sn
    - Use lower HT temperatures
- Both result in lower  $J_c$



High  $J_c$ , RRR when  $D_{eff} \sim 50-60 \mu$ m

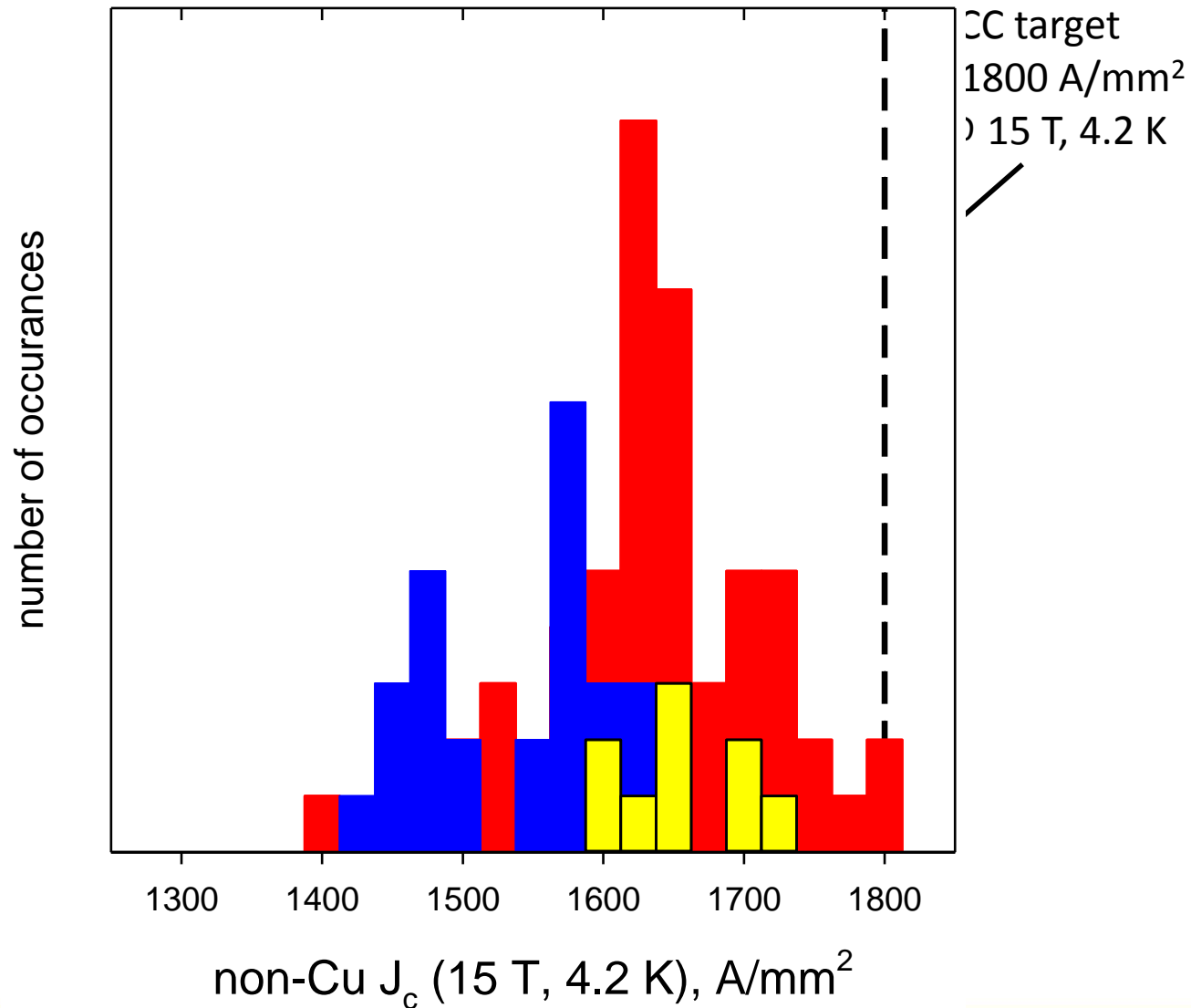
# Reducing manufacturing variation might get us close to the target $J_c$ performance

Needed  $J_c$  improvement may be modest when:

$60 \mu\text{m } D_{\text{eff}}$

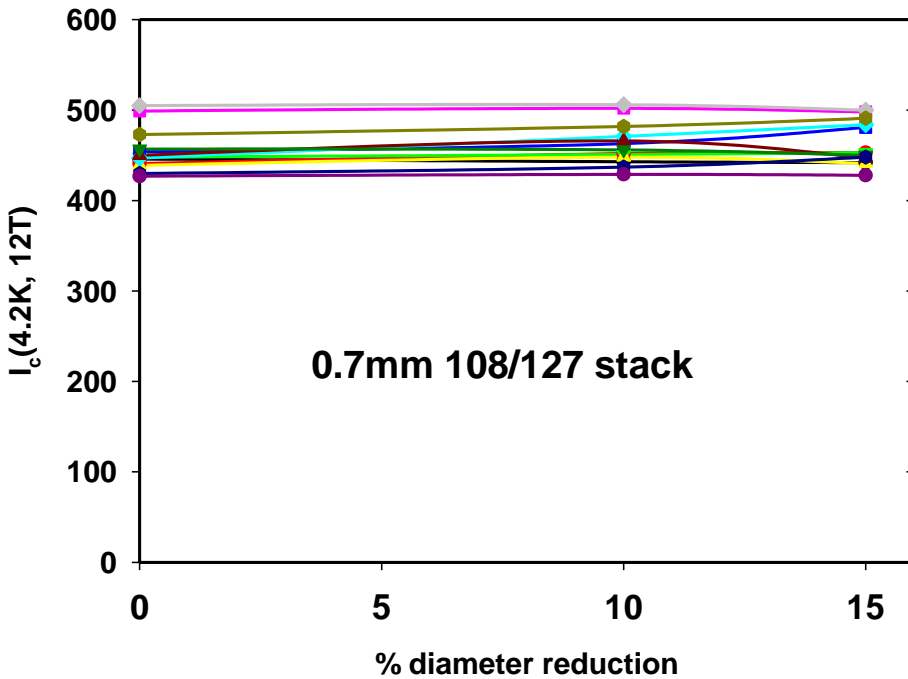
$\text{RRR} > 100$

- Near term R&D work will focus on maximizing  $J_c$  when  $D_{\text{eff}} \sim 60 \mu\text{m}$
- Step change may need to come from e.g. artificial pinning centers

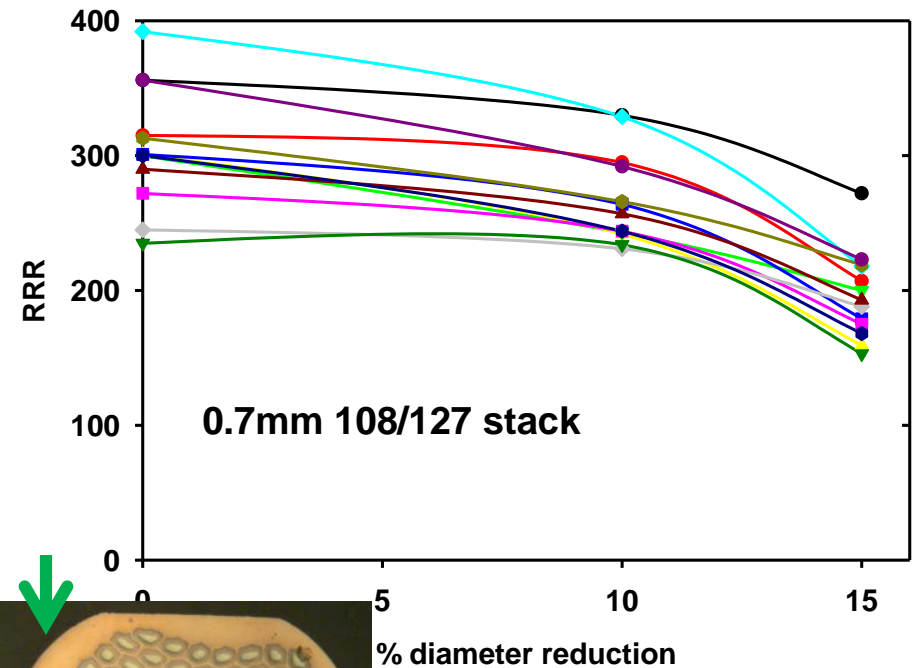


# High RRR, $J_c$ maintained after cabling

- $I_c$  values are maintained through >15% rolling

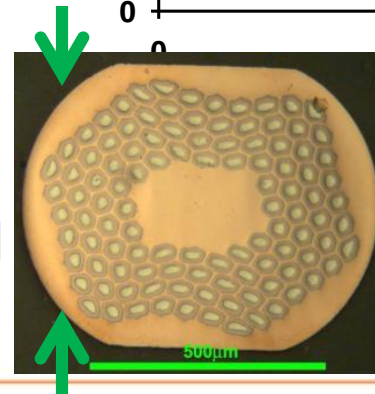


- RRR decreases >10% rolling, but remains >150



RRP® is compatible with Rutherford cabling

15% rolled



# Comparison of Nb-Ti and Nb<sub>3</sub>Sn production scale and cost drivers

Parameter	Nb-Ti	Nb <sub>3</sub> Sn	Cost challenge
Nb content	18 wt%	26 wt%	Nb is most expensive raw material (Cu:SC 1.3 assumed)
Strand billet size	400 kg	40 kg	Limited Nb <sub>3</sub> Sn piece lengths
Billet stacking steps	2	3	↑ Labor and time costs, also yield loss at each step
Ongoing demand (infra-structure)	1000's tons per year	10's tons per year	<ul style="list-style-type: none"> <li>• LHC was a fraction of annual Nb-Ti market</li> <li>• <b>FCC (6000 tons/5 yrs) would be &gt;50x base Nb<sub>3</sub>Sn market</b></li> </ul>

Nb<sub>3</sub>Sn market is different from Nb-Ti; FCC demand would dominate

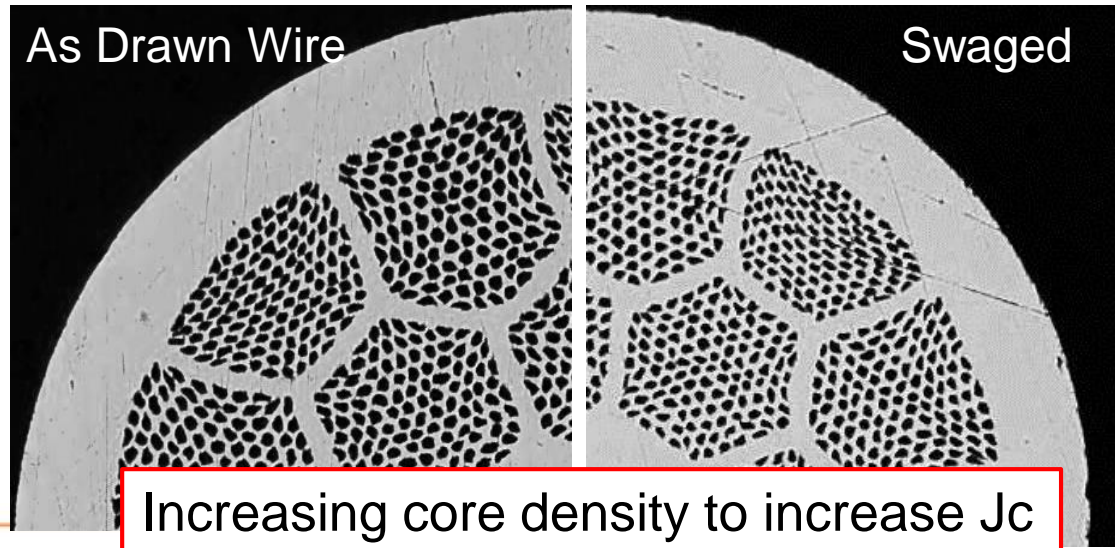
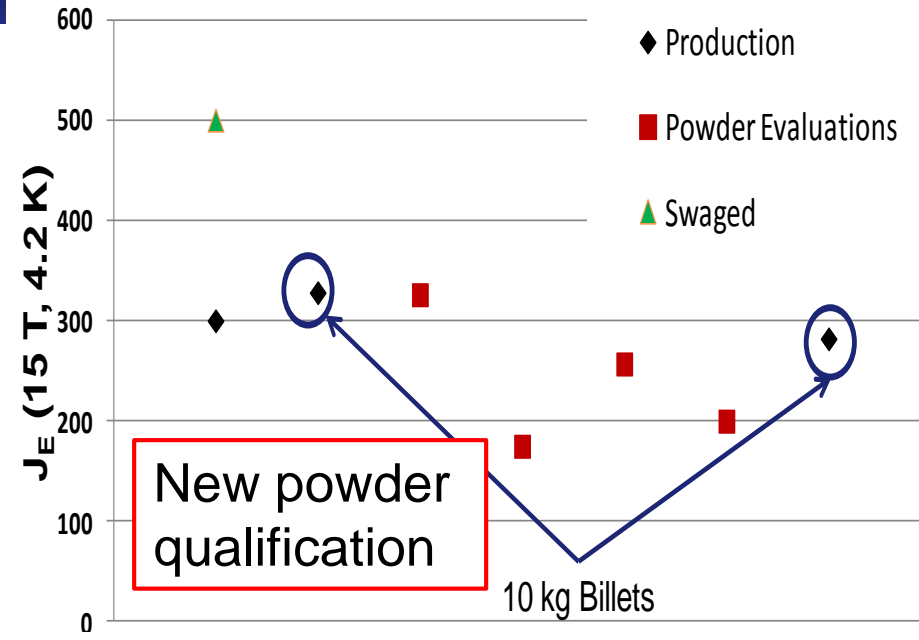
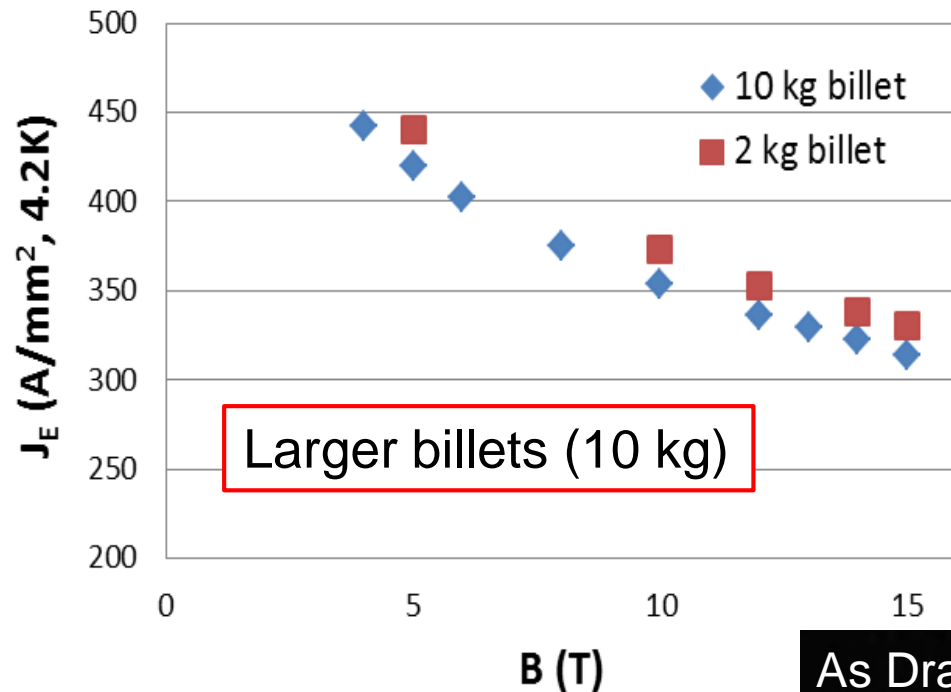
- Potential cost reduction contributions:
    - + Raw materials: ? Market driven
    - + Incremental Conductor Improvement: ~10% J<sub>c</sub> gain
    - + Efficiency gains from scale up of billet sizes
    - + Continued incremental piece length gains
- 

Together these may reduce \$/kA-m cost by ~  $\frac{1}{3}$

To cut the \$/kA-m by  $\frac{2}{3}$  requires a more significant J<sub>c</sub> gain

- Layer J<sub>c</sub> increase could yield largest cost benefit- provided conductor fabrication cost is not increased cost elsewhere

# Progress with Bi-2212



- Increasingly consistent properties billet to billet
- $J_E$  (16 T) now about  $\frac{2}{3}$  that of Nb<sub>3</sub>Sn strands

# Cost: Opportunity in \$/kA-m, Not Materials

- Silver
  - No known alternatives, metals market dictates price
  - 2212 fill factor limited to ~30% (already achieved)
- Powders
  - Significant overhead costs dominate today
  - Modest annual volumes do not drive cost reductions
- Production Scale Comparisons:

	Bi-2212	Internal Tin (w/o ITER)	Internal Tin (For ITER)	Nb-Ti (MRI)
Approximate Billet Mass (kg)	10	30	60	400
Approximate Annual Market (tons)	0.01	10's	100's	1000's

- $(J_c - RRR - D_{eff})$  of today's  $Nb_3Sn$  is well optimized
- FCC requirements stretch beyond the state of the art
  - Target  $J_c$  & RRR are “close” for  $D_{eff} \sim 60 \mu m$
  - Basic R&D again required for  $Nb_3Sn$  layer  $J_c$  breakthrough
  - HEP-specific development requires sustained HEP “pull”
- And then, there's cost...
  - Scale up can help reduce cost, *if demand is consistent*
  - $Nb_3Sn$  is not Nb-Ti; FCC would be the market
- Opportunities
  - R&D today supports conductor in production 2025-2030
  - Layer  $J_c$  breakthrough (for free!) may solve cost challenge